

METHODS OF IMPROVEMENT OF PROPERTIES
OF THE OXIDE LAYER-SILICON CARBIDE
INTERFACE

A.B. Okhrimenko

V. Lashkaryov Institute of Semiconductor Physics,
Nat. Acad. of Sci. of Ukraine
(41, Prosp. Nauky, Kyiv 03680, Ukraine;
e-mail: *olga@isp.kiev.ua*)

S u m m a r y

The structure of defects appearing on the SiO₂/SiC interface is considered. The effects of external actions and an additional processing on defect states on the SiO₂/SiC interface are analyzed. A possibility to use alternative oxides (in particular, ZrO₂, Al₂O₃, TiO₂, Gd₂O₃, and Er₂O₃) as a blocking dielectric layer is discussed.